

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13	sputter\$3 with (chromium metal) with n\$type with semiconductor with contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 10:24
L2	310	438/676	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:19
L3	136	2 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:21
L4	4	3 and (GAN gallium with nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:21
L5	1820	438/29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:23
L6	1216	5 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:23
L8	268	6 and (gan gallium with nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:23

L9	122	8 and sputter\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:24
L10	11	257/E21.053	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:29
L11	19	257/E21.352	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:30
L12	1	((GAN gallium \$1nitride) and compound and semiconductor and light\$1emitt\$3 and P \$1type and positive and electrode and negative and sputter \$3).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/03 11:31
S1	0	(GAN gallium\$1nitride) with compound with semiconductor and light\$1emitt\$3 with (GAN gallium\$1nitride) and P\$1type with (GAN gallium\$1nitride) and positive with electrode and negative with electrode and (bond bonding) with pad and contact and sputter\$3 with (chrome chromium Or \$1alloy\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:26
S2	4776	(GAN gallium\$1nitride) with compound with semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:27

S3	598	(GAN gallium\$1nitride) with compound with semiconductor and light\$1emitt\$3 with (GAN gallium\$nitride) and P\$1type with (GAN gallium\$nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:27
S4	72	(GAN gallium\$1nitride) with compound with semiconductor and light\$1emitt\$3 with (GAN gallium\$nitride) and P\$1type with (GAN gallium\$nitride) and positive with electrode and negative with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:27
S5	22	(GAN gallium\$1nitride) with compound with semiconductor and light\$1emitt\$3 with (GAN gallium\$nitride) and P\$1type with (GAN gallium\$nitride) and positive with electrode and negative with electrode and (bond bonding) with pad and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:27
S6	0	S5 and chrome	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:28
S7	2	S5 and chromium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:28
S8	0	S6 and sputter\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:28

S9	2	"20030194826"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:57
S10	10	"5422500"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 15:57
S11	37	(GAN gallium\$1nitride) and light\$1emitt\$3 with (GAN gallium \$nitride) and P\$1type with (GAN gallium \$nitride) and positive with electrode and negative with electrode and (bond bonding) with pad and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:10
S12	11	(GAN gallium\$1nitride) with compound with semiconductor and sputter\$3 with (chromium chrome chrome\$alloy cr\$alloy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:10
S13	617	438/21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:13
S14	61	S13 and (chromium chrome chrome\$alloy cr\$alloy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:13
S15	1	S14 and GAN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:13

S16	1	S14 and (GAN Gallium nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:14
S17	2369	438/22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:32
S18	271	S17 and (chromium chrome alloy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:32
S19	70	S18 and (GAN Gallium nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:33
S20	41	S19 and sputter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:33
S21	0	S19 and sputter with chrome	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:33
S22	2	S19 and sputter with cr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:33
S23	2	S19 and sputter with chromium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/21 17:33

S24	4	(GAN gallium\$1nitride) with compound with semiconductor and LED and sputter\$3 with (Cr\$alloy chrome chromium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/22 13:37
S26	9	(GAN gallium\$1nitride) with compound with semiconductor and (LED light with diode) and sputter\$3 with (Cr\$alloy chrome chromium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/22 13:42
S27	18	(GAN gallium\$1nitride) with semiconductor and (LED light with diode) and sputter\$3 with (Cr\$alloy chrome chromium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/22 13:44
S28	9	S27 not S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/22 13:44
S29	13472	sputter\$3 with (chrome chrome\$alloy \$1 Cr with alloy chromium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:15
S30	74	S29 and (GAN Gallium \$nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:15
S31	1450	438/46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:23
S32	987	438/47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:23

S33	11	(S31 S32) and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:23
S34	13472	sputter\$3 with (chrome chrome\$alloy \$1 Cr with alloy chromium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:29
S35	74	S34 and (GAN Gallium \$nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:29
S36	1450	438/46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:29
S37	987	438/47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:29
S38	3	(S36 S37) and S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:29
S39	942	(GAN Gallium\$nitride) and (S36 S37)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:30
S40	705	S39 and n\$type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:30

S41	678	S40 and p-type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:39
S42	239	S41 and light-emitt\$3 with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:42
S43	0	S42 and pad and contact and chrome	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:42
S44	73	S42 and pad and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:42
S45	20	S44 and sputter\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:43
S46	4	"6713789"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:48
S47	2	"20040115917"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 10:49
S48	1	09/516177	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 11:38

S49	4	"6713789"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 11:39
S50	111	electrode and p-type with Gan with contact and n-type with GAN with contact and INGAN with light and pad and contact and sputter\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 17:10
S51	22	"6067309"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 17:13
S52	9	"6100174"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 17:13
S53	4	"6713789"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 17:16
S54	0	(GAN gallium\$1nitride) with compound with semiconductor and light\$1emitt\$3 with (GAN gallium\$nitride) and P\$1type with (GAN gallium\$nitride) and positive with electrode and negative with electrode and (bond bonding) with pad and contact and (sputter\$3 PVD deposition) with (chrome chromium Cr \$1alloy\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 17:21

S55	12	sputter\$3 with metal with n\$type with semiconductor with contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/25 17:45
S56	4	(GAN gallium\$1nitride) with compound with semiconductor and (bond bonding) with pad and contact and sputter\$3 with (chrome chromium Cr \$1alloy\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 18:04

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